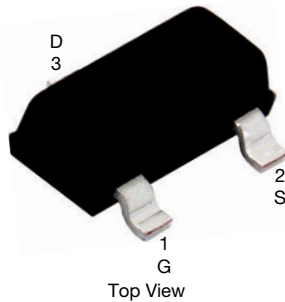


## N-Channel 20 V (D-S) MOSFET

SOT-23 (TO-236)



Top View

Marking code: N2

PRODUCT SUMMARY	
$V_{DS}$ (V)	20
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 4.5$ V	0.057
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 2.5$ V	0.075
$Q_g$ typ. (nC)	3.5
$I_D$ (A)	2.9
Configuration	Single

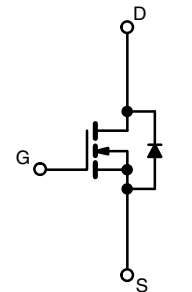
### FEATURES

- TrenchFET® power MOSFET
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
 COMPLIANT  
 HALOGEN  
**FREE**  
 Available

### APPLICATIONS

- Load switching for portable devices
- DC/DC converter



N-Channel MOSFET

ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free	Si2302CDS-T1-E3
Lead (Pb)-free and halogen-free	Si2302CDS-T1-GE3

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)					
PARAMETER	SYMBOL	5 S	STEADY STATE	UNIT	
Drain-source voltage	$V_{DS}$	20	20	V	
Gate-source voltage	$V_{GS}$	$\pm 8$	$\pm 8$		
Continuous drain current ( $T_J = 150$ °C) <sup>a</sup>	$I_D$	$T_A = 25$ °C	2.9	2.6	A
		$T_A = 70$ °C	2.3	2.1	
Pulsed drain current <sup>b</sup>	$I_{DM}$	10	10		
Continuous source current (diode conduction) <sup>a</sup>	$I_S$	0.72	0.6		
Power dissipation <sup>a</sup>	$P_D$	$T_A = 25$ °C	0.86	0.71	W
		$T_A = 70$ °C	0.55	0.46	
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	-55 to +150	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum junction-to-ambient <sup>a</sup>	$R_{thJA}$	$t \leq 5$ s	120	145	°C/W
		Steady state	140	175	
Maximum junction-to-foot	$R_{thJF}$	62	78		

### Notes

- Surface mounted on 1" x 1" FR4 board
- Pulse width limited by maximum junction temperature



SPECIFICATIONS (T <sub>A</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN.	TYP.	MAX.	
<b>Static</b>						
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	20	-	-	V
Gate-threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	0.40	-	0.85	
Gate-body leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 8 V	-	-	± 100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V	-	-	0.1	μA
		V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 50 °C	-	-	4	
		V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C	-	-	15	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 10 V, V <sub>GS</sub> = 4.5 V	6	-	-	A
Drain-source on-resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 3.6 A	-	0.045	0.057	Ω
		V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 3.1 A	-	0.056	0.075	
Forward transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 3.6 A	-	13	-	S
Diode forward voltage	V <sub>SD</sub>	I <sub>S</sub> = 0.95 A, V <sub>GS</sub> = 0 V	-	0.7	1.2	V
<b>Dynamic <sup>b</sup></b>						
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 3.6 A	-	3.5	5.5	nC
Gate-source charge	Q <sub>gs</sub>		-	0.6	-	
Gate-drain charge	Q <sub>gd</sub>		-	0.45	-	
Gate resistance	R <sub>g</sub>	f = 1 MHz	2	4	8	Ω
<b>Switching</b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 10 V, R <sub>L</sub> = 2.78 Ω I <sub>D</sub> ≅ 3.6 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω	-	8	15	ns
Rise time	t <sub>r</sub>		-	7	15	
Turn-off delay time	t <sub>d(off)</sub>		-	30	45	
Fall time	t <sub>f</sub>		-	7	15	
Source-drain reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 3.6 A, di/dt = 100 A/μs	-	8.5	15	nC
Body diode reverse recovery charge	Q <sub>rr</sub>		-	2	4	

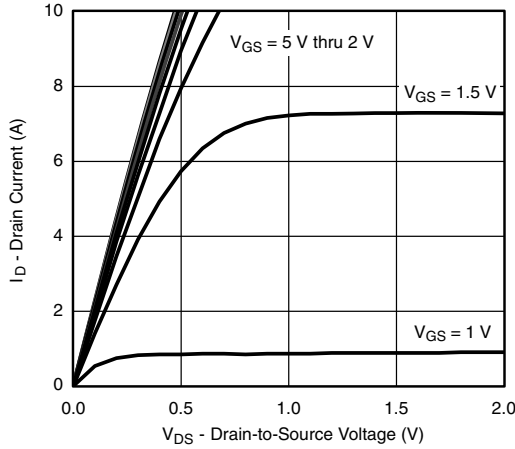
**Notes**

- a. Pulse test: Pulse width ≤ 300 μs, duty cycle ≤ 2 %  
b. Guaranteed by design, not subject to production testing

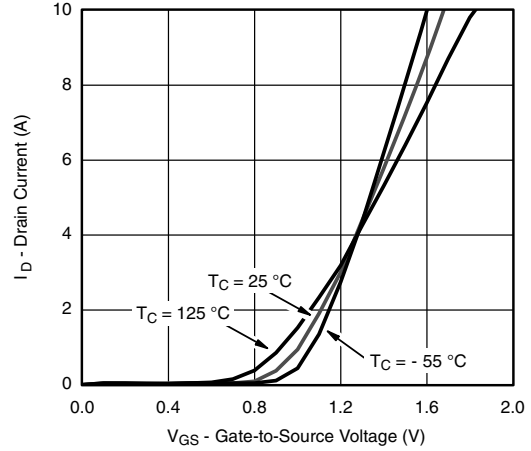
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



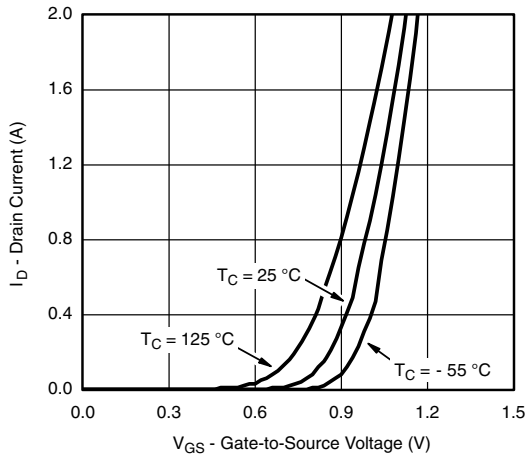
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



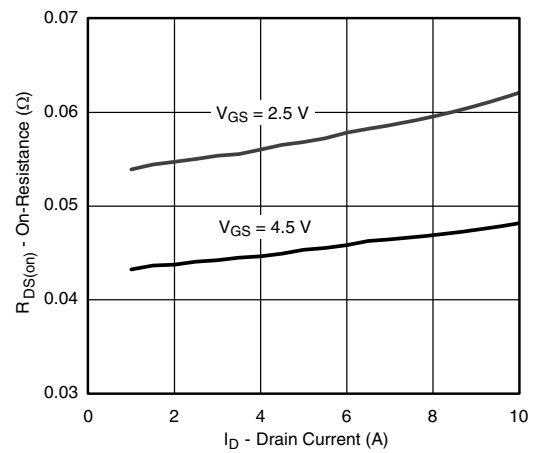
Output Characteristics



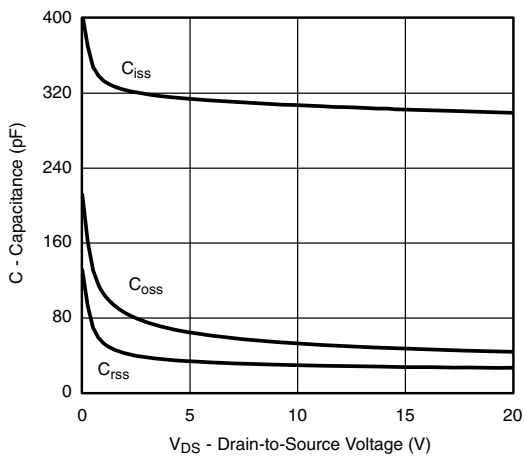
Transfer Characteristics



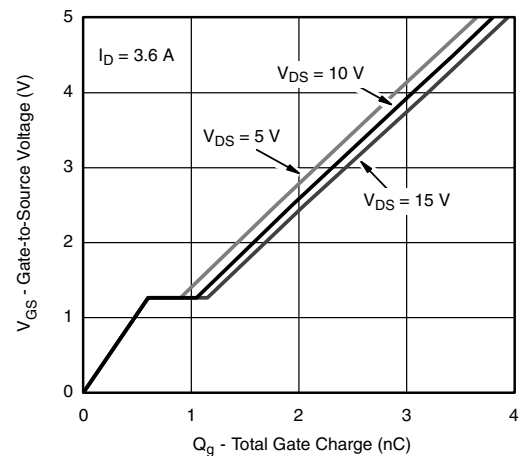
Transfer Characteristics



On-Resistance vs. Drain Current

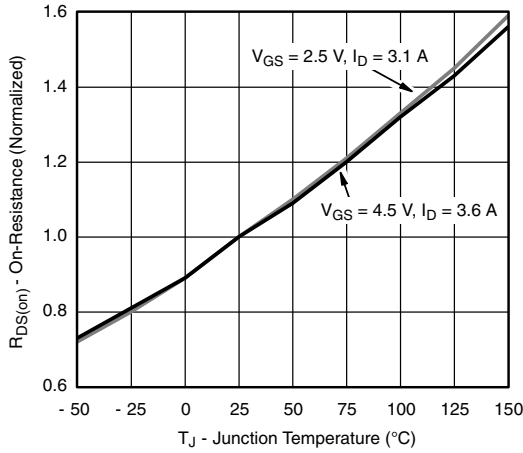


Capacitance

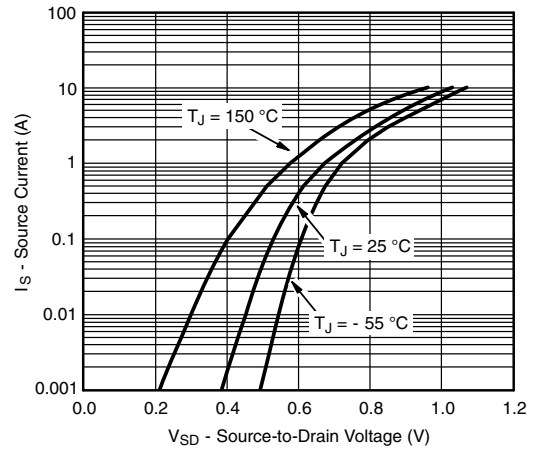


Gate Charge

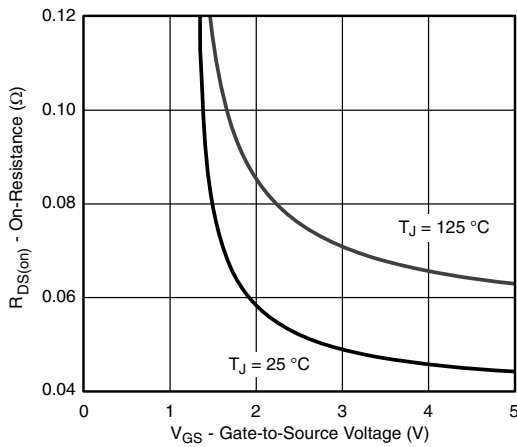
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



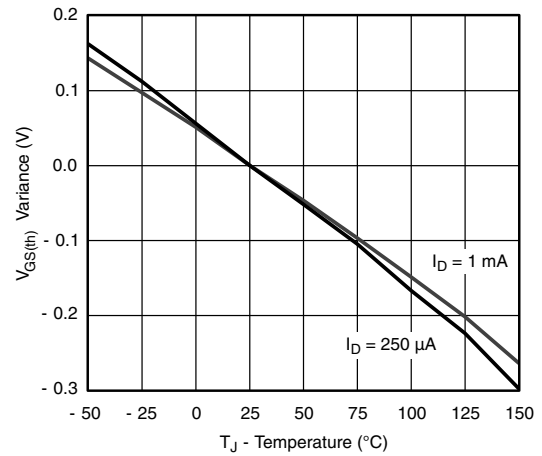
**On-Resistance vs. Junction Temperature**



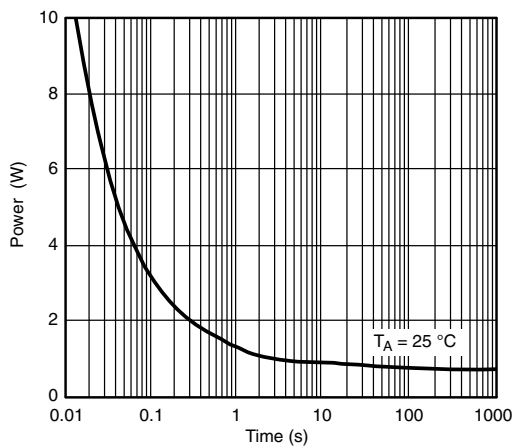
**Source-Drain Diode Forward Voltage**



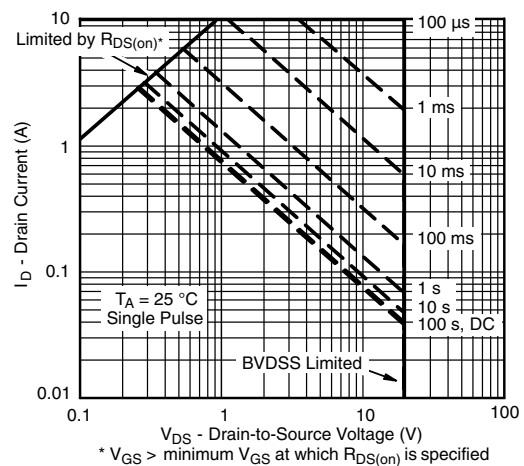
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



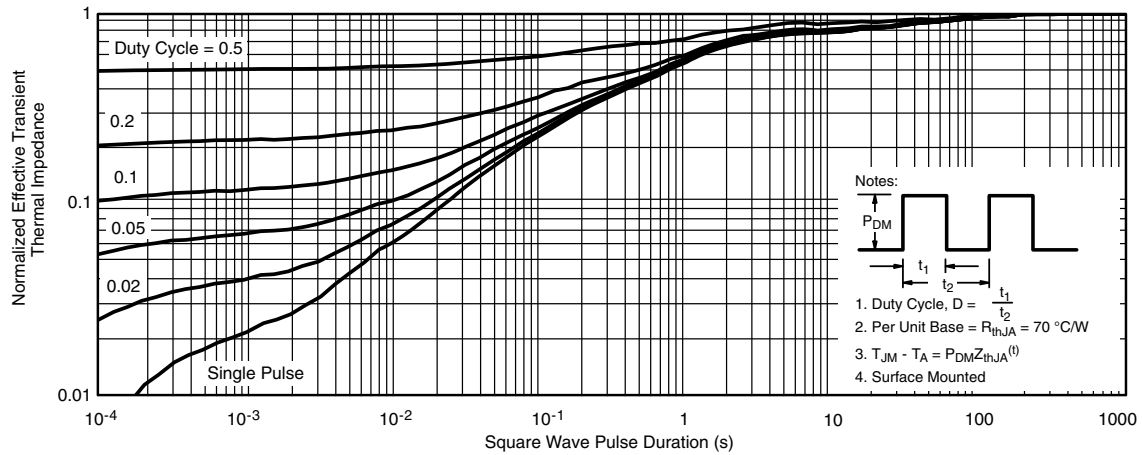
**Single Pulse Power**



**Safe Operating Area, Junction-to-Ambient**



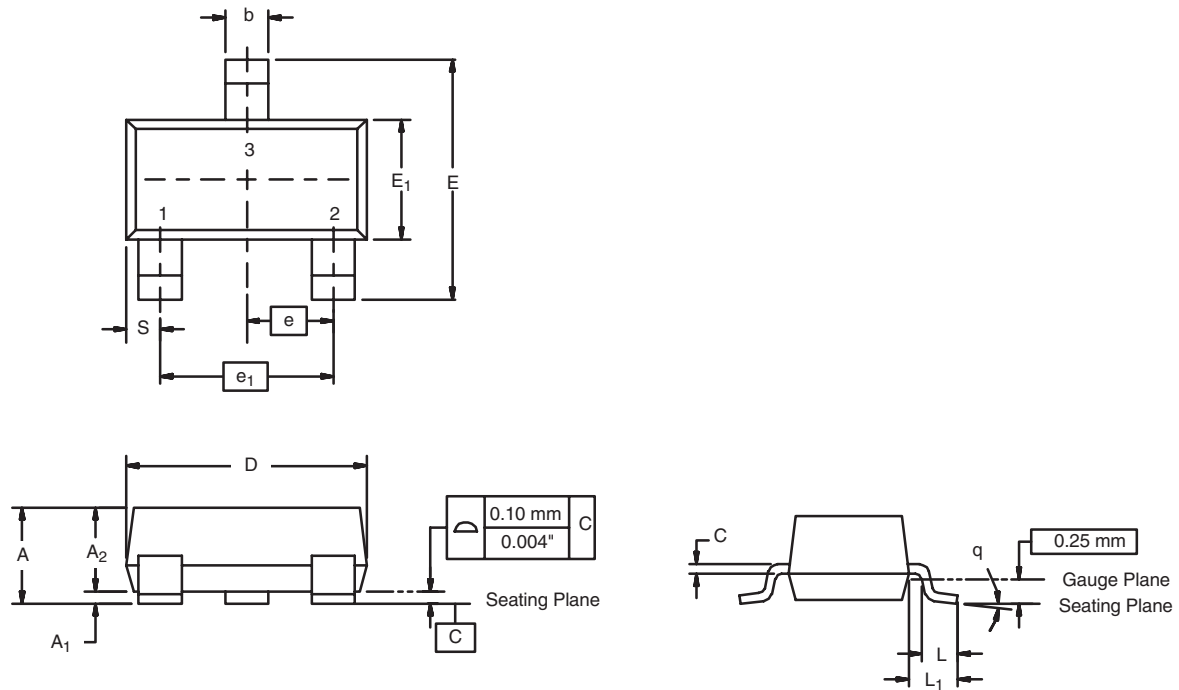
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?68645](http://www.vishay.com/ppg?68645).

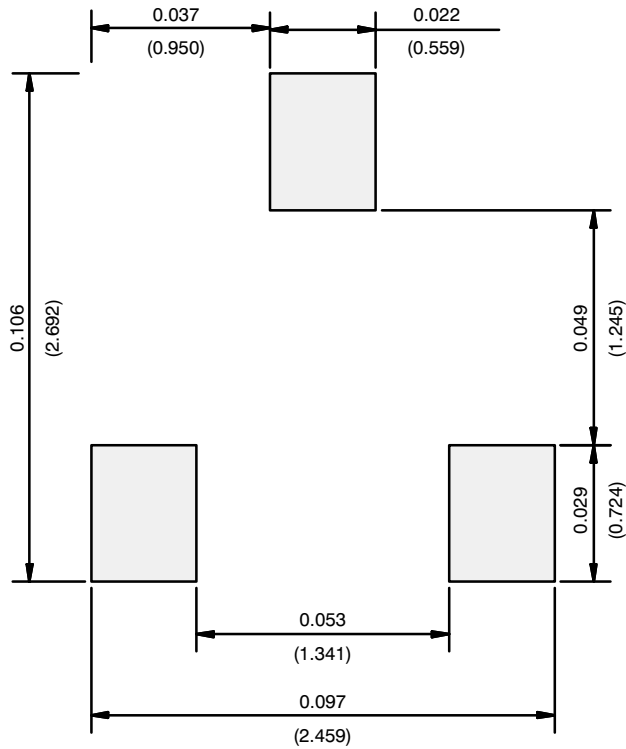
## SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A <sub>1</sub>	0.01	0.10	0.0004	0.004
A <sub>2</sub>	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E <sub>1</sub>	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e <sub>1</sub>	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L <sub>1</sub>	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°

ECN: S-03946-Rev. K, 09-Jul-01  
 DWG: 5479

## RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads  
Dimensions in Inches/(mm)

[Return to Index](#)



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